

EPEE 550 PECVD

System Overview

EPEE 550 PECVD is an indispensable process tool used in the manufacturing of LED chips and composite substrates. It is widely used in the deposition of SiO and SiN_x dielectric films for LED blue-green and red-yellow devices and the high-speed deposition of SiO thick films on patterned sapphire substrates (PSS). In addition, the EPEE 550 PECVD tool supports high uniformity and low stress SiN_x thin film deposition which can be applied to the development and mass production of third-generation semiconductor power devices.



EPEE 550 PECVD

Substrate Size:	50 mm, 100 mm, 150 mm, 200 mm
Deposition Film:	SiO, SiN _x , SiON
Applications:	Passivation layers, current block layers, mask layers, insulator
Technology Markets:	LED
Tray Capacity:	73 x 50mm, 19 x 100 mm, 8 x 150 mm, 4 x 200mm

Processes

- LED: SiO₂, SiN_x, SiON thin film
- Power: SiN_x film

Production Advantages

- Excellent film uniformity and stress control to meet the high-quality process requirements of power devices
- Optional secondary RF source to effectively adjust film stress
- High throughput design
- Efficient in-situ plasma chamber cleaning with high power plasma source
- Easy wafer load & unload with air-actuated chamber lid